TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (π- MOSIV)

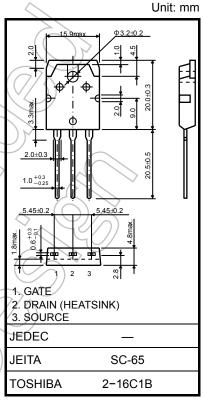
2SK4115

Switching Regulator Applications

- Low drain-source ON-resistance: $R_{DS(ON)} = 1.6 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fS}| = 5.0 \text{ S (typ.)}$
- Low leakage current: $I_{DSS} = 100 \mu A (max) (V_{DS} = 720 V)$
- Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_D = 1 mA)

Absolute Maximum Ratings (Ta = 25°C)

$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						1.1	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Characteristic			Symbol	Rating	Unit	
Gate-source voltage VGSS ±30 V Drain current DC (Note 1) ID T A Pulse (Note 1) IDP 21 A Drain power dissipation (Tc = 25°C) PD 150 W Single pulse avalanche energy (Note 2) EAS 491 mJ Avalanche current IAR 7 A Repetitive avalanche energy (Note 3) EAR 15 mJ Channel temperature Tch 150 °C	Drain-source voltage	Drain-source voltage			900	$\langle v \rangle$	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)			V_{DGR}	900	V	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate-source voltage			V_{GSS}	±30	V	
Pulse (Note 1) I _{DP} 21 Drain power dissipation (Tc = 25°C) P _D 150 W Single pulse avalanche energy (Note 2) E _{AS} 491 mJ Avalanche current I _{AR} 7 A Repetitive avalanche energy (Note 3) E _{AR} 15 mJ Channel temperature T _{Ch} 150 °C	Drain current	DC	(Note 1)	I _D	7	^	
Single pulse avalanche energy (Note 2) Avalanche current Repetitive avalanche energy (Note 3) Channel temperature EAS 491 MJ The pulse avalanche energy (Note 3) The pulse avalanche energy (Note 3)	Drain current	Pulse	(Note 1)	I _{DP}	21	Α	
Avalanche current IAR 7 A Repetitive avalanche energy (Note 3) EAR 15 mJ Channel temperature T _{ch} 150 °C	Drain power dissipa	Drain power dissipation (Tc = 25°C)			150	W	
Repetitive avalanche energy (Note 3) EAR 15 mJ Channel temperature T _{ch} 150 °C				E _{AS}	491	mJ	
Channel temperature T _{Ch} 150 °C	Avalanche current			I _{AR})) 7	Α	
	Repetitive avalanche energy (Note 3)			EAR	15	mJ	
Storage temperature range T _{stg} –55 to 150 °C	Channel temperatur	Channel temperature			150	∫/°C	
	Storage temperature range			Tstg	-55 to 150	/_ec	



Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

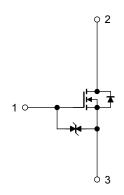
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	Rth (ch-c)	0.833	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	50	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C during use of the device.

Note 2: $V_{DD} = 90 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$, L = 18.4 mH, $R_G = 25 \Omega$, $I_{AR} = 7 \text{ A}$

Note 3: Repetitive rating: pulse width limited by max junction temperature

This transistor is an electrostatic-sensitive device. Handle with care.



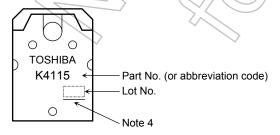
Electrical Characteristics (Ta = 25°C)

Char	acteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА	
Gate-source brea	kdown voltage	V (BR) GSS	$I_G=\pm 10~\mu A,~V_{DS}=0~V$	±30	_	_	V	
Drain cutoff curre	nt	I _{DSS}	V _{DS} = 720 V, V _{GS} = 0 V	7	_	100	μΑ	
Drain-source brea	akdown voltage	V (BR) DSS	$I_D = 10$ mA, $V_{GS} = 0$ V	900	/	_	V	
Gate threshold vo	oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0) /_	4.0	V	
Drain-source ON-	-resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 3.5 A) 	1.6	2.0	Ω	
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 3.5 A	2.6	5.0	_	S	
Input capacitance	•	C _{iss})	1650	_		
Reverse transfer	capacitance	C _{rss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	_	30	_	pF	
Output capacitan	Output capacitance			_	140	_		
Switching time	Rise time	t _r	10 V VGS D=3.5 A	-(50	7		
	Turn-on time	t _{on}	0 V		90) —		
	Fall time	t _f	$R_{L} = 114 \Omega$		70		ns	
	Turn-off time	t _{off}	Duty \leq 1%, $t_W = 10 \mu s$ $V_{DD} \approx 400 \text{ V}$		240			
Total gate charge (gate-source plus gate-drain)		Qg		_	45	_		
Gate-source charge		Q _{gs}	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 7 \text{ A}$	_	24	_	nC	
Gate-drain ("Miller") charge		Qgd	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		21			

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	7	Α
Pulse drain reverse current (Note 1)	IDRP		_	_	21	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 7 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	∕> t _{rr}	$I_{DR} = 7 \text{ A}, V_{GS} = 0 \text{ V},$	_	1400	_	ns
Reverse recovery charge	Qrr	dI _{DR} /dt = 100 A/μs		12		μС

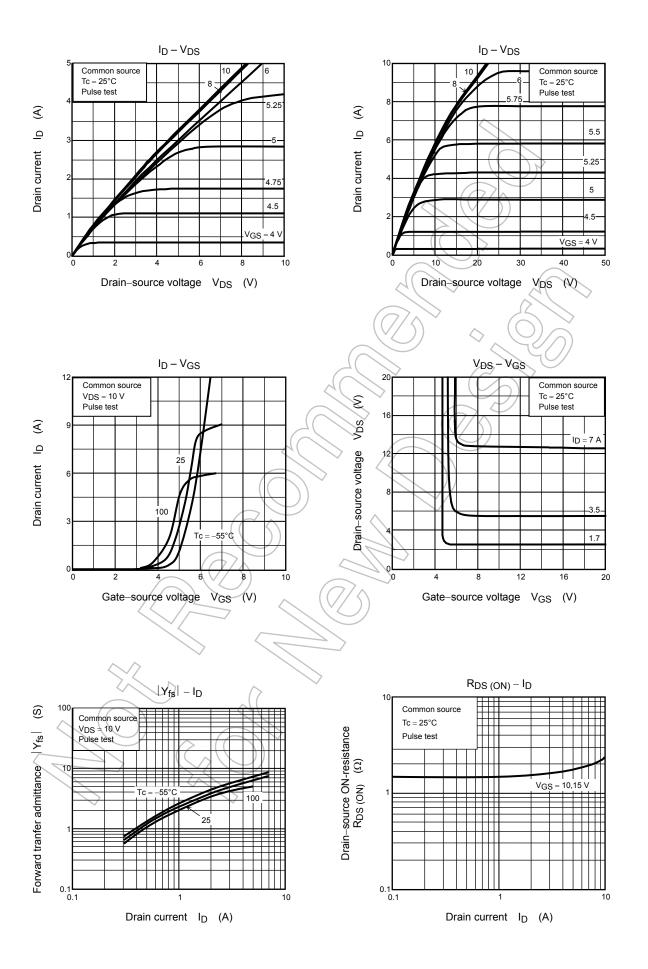
Marking

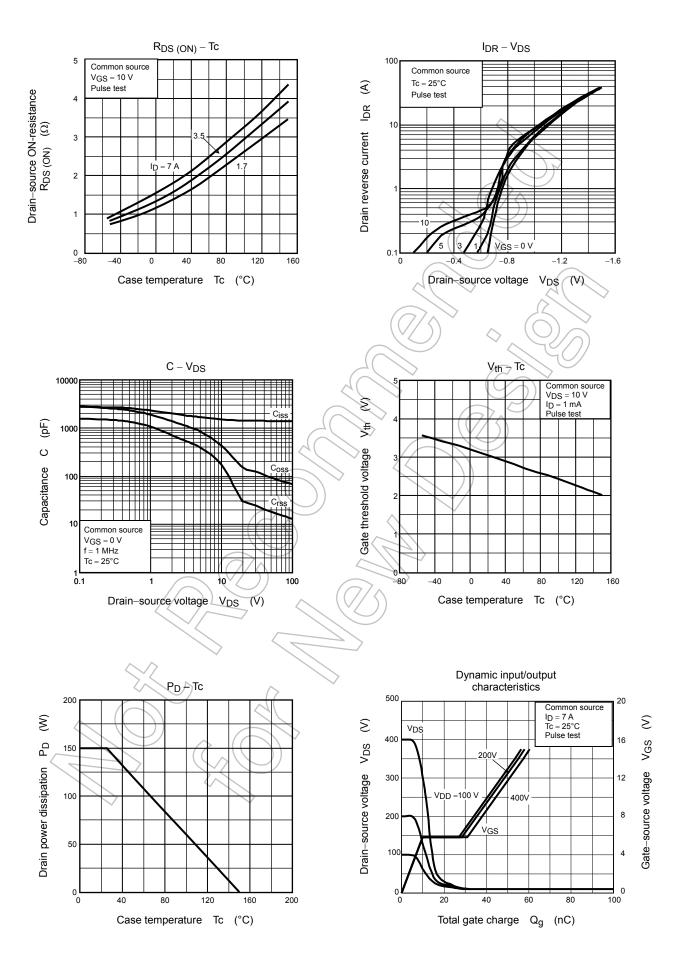


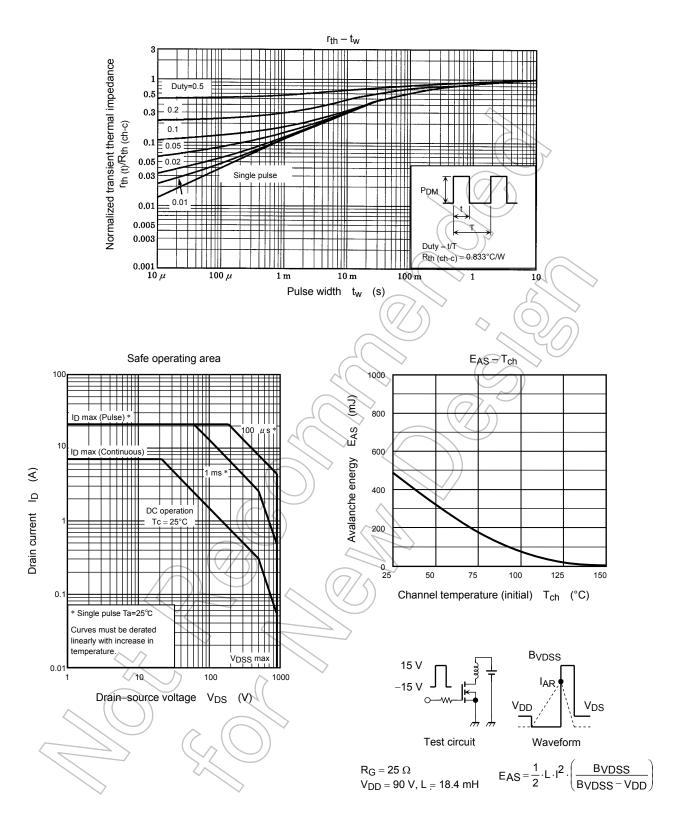
Note 4: A line under a Lot No. identifies the indication of product Labels.

[[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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